NSN 5962-01-335-4446

Memory Microcircuit - Page 1 of 2

View Online at https://aerobasegroup.com/nsn/5962-01-335-4446

Overall Height:

0.400 inches

Body Length:

0.840 inches

Body Width:

Between 0.220 inches and 0.310 inches

Body Height:

Between 0.140 inches and 0.185 inches

Maximum Power Dissipation Rating:

739.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

W/active pull-up and 3-state output and high impedance and monolithic and bipolar and schottky and programmable

Inclosure Material:

Ceramic

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

10 input

Case Outline Source And Designator:

D-2 mil-m-38510

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

7.0 volts power source

Time Rating Per Chacteristic:

75.00 nanoseconds propagation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Rom

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0